

Silicon General Purpose Bridge Rectifier

COMCHIP
SMD DIODE SPECIALIST



B05S-G thru B10S-G

Glass Passivated Type

Reverse Voltage: 50 ~ 1000 Volts

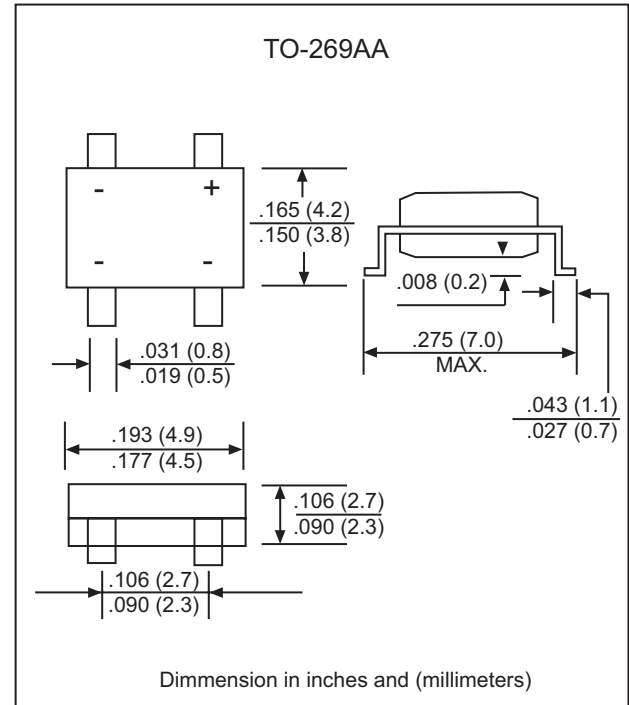
Forward Current: 0.5 Amp

Features:

- Ideal for surface mount applications
- Easy pick and place
- Plastic package has Underwriters Lab. Flammability classification 94V-0
- Built-in strain relief
- Glass passicated junction

Mechanical Data:

- Case: JEDEC DO-269AA molded plastic
- Terminals: solderable per MIL-STD-750, Method 2026
- Polarity: Marked on body
- Mounting position: Any
- Approx. Weight: 0.22gram



Maximum Ratings and Electrical Characteristics

Parameter	Symbol	B05S-G	B1S-G	B2S-G	B4S-G	B6S-G	B8S-G	B10S-G	Unit
Max. Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Max. DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Max. RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Peak Surge Forward Current 8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}	30							A
Max. Average Forward Current	I_O	0.5							A
Max. Instantaneous Forward Current at 0.5A	V_F	1.0							V
Max. DC Reverse Current at Rated DC Blocking Voltage $T_a=25^{\circ}C$ $T_a=125^{\circ}C$	I_R	5 500							μA
Max. Thermal Resistance (Note 1)	$R_{\theta JA}$	85							$^{\circ}C/W$
Operating Junction Temperature	T_j	-55 to +150							$^{\circ}C$
Storage Temperature	T_{STG}	-55 to +150							$^{\circ}C$

Note1: Thermal resistance from junction to ambient.

"-G" suffix designated RoHS compliant version



B05S-G thru B10S-G

Rating and Characteristic Curves (B05S-G thru B10S-G)

Fig. 1 - Reverse Characteristics

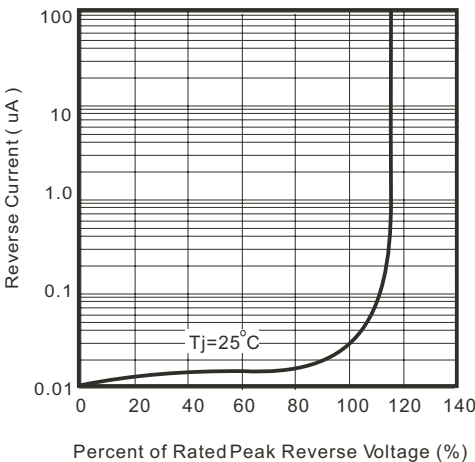


Fig.2 - Forward Characteristics

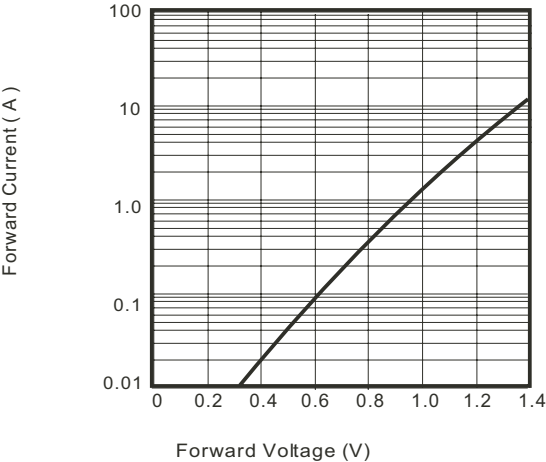


Fig. 3 - Non Repetitive Forward Surge Current

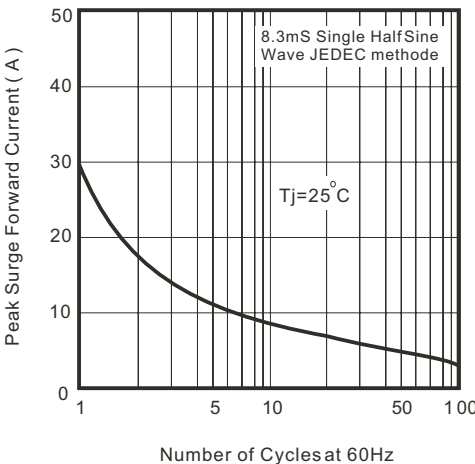


Fig. 4 - Current Derating Curve

